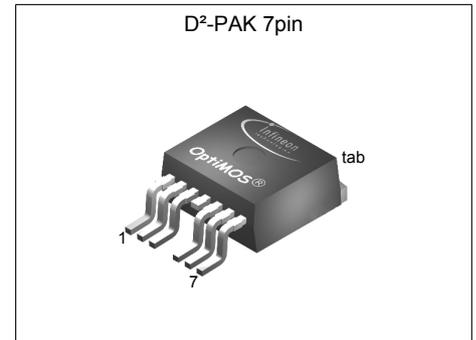


# MOSFET

## OptiMOS™ 5 Power-Transistor, 100 V

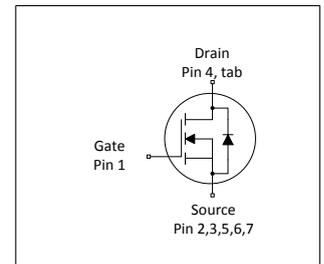
### Features

- Ideal for high frequency switching and sync. rec.
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit       |
|------------------|-------|------------|
| $V_{DS}$         | 100   | V          |
| $R_{DS(on),max}$ | 3.2   | m $\Omega$ |
| $I_D$            | 166   | A          |
| $Q_{oss}$        | 98    | nC         |
| $Q_G(0V..10V)$   | 76    | nC         |



| Type / Ordering Code | Package    | Marking  | Related Links |
|----------------------|------------|----------|---------------|
| IPB032N10N5          | PG-TO263-7 | 032N10N5 | -             |

<sup>1)</sup> J-STD20 and JESD22

## Table of Contents

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                          | Symbol            | Values |      |            | Unit | Note / Test Condition                             |
|------------------------------------|-------------------|--------|------|------------|------|---|
|                                    |                   | Min.   | Typ. | Max.       |      |   |
| Continuous drain current           | $I_D$             | -      | -    | 166<br>118 | A    | $T_C=25\text{ °C}$<br>$T_C=100\text{ °C}$         |
| Pulsed drain current <sup>1)</sup> | $I_{D,pulse}$     | -      | -    | 664        | A    | $T_C=25\text{ °C}$                                |
| Avalanche energy, single pulse     | $E_{AS}$          | -      | -    | 233        | mJ   | $I_D=100\text{ A}$ , $R_{GS}=25\text{ }\Omega$    |
| Gate source voltage                | $V_{GS}$          | -20    | -    | 20         | V    | -   |
| Power dissipation                  | $P_{tot}$         | -      | -    | 187        | W    | $T_C=25\text{ °C}$                                |
| Operating and storage temperature  | $T_j$ , $T_{stg}$ | -55    | -    | 175        | °C   | IEC climatic category;<br>DIN IEC 68-1: 55/175/56 |

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter  | Symbol     | Values |      |      | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-----------------------|
|  |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case  | $R_{thJC}$ | -      | 0.5  | 0.8  | K/W  | -                     |
| Thermal resistance, junction - ambient, minimal footprint                            | $R_{thJA}$ | -      | -    | 62   | K/W  | -                     |
| Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area <sup>2)</sup> | $R_{thJA}$ | -      | -    | 40   | K/W  | -                     |
| Soldering temperature and reflow soldering is allowed                                | $T_{sold}$ | -      | -    | 260  | °C   | reflow MSL1           |

<sup>1)</sup> see Diagram 3

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

### 3 Electrical characteristics

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |            |            | Unit             | Note / Test Condition   |
|----------------------------------|---------------|--------|------------|------------|------------------|---|
|                                  |               | Min.   | Typ.       | Max.       |                  |   |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 100    | -          | -          | V                | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$   |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.2    | 3.0        | 3.8        | V                | $V_{DS}=V_{GS}$ , $I_D=125\text{ }\mu\text{A}$  |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.1<br>10  | 1<br>100   | $\mu\text{A}$    | $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$<br>$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 1          | 100        | nA               | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$  |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 2.8<br>3.4 | 3.2<br>4.2 | $\text{m}\Omega$ | $V_{GS}=10\text{ V}$ , $I_D=83\text{ A}$<br>$V_{GS}=6\text{ V}$ , $I_D=42\text{ A}$   |
| Gate resistance <sup>1)</sup>    | $R_G$         | -      | 1.3        | 2          | $\Omega$         | -   |
| Transconductance                 | $g_{fs}$      | 84     | 168        | -          | S                | $ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=83\text{ A}$  |

**Table 5 Dynamic characteristics<sup>1)</sup>**

| Parameter                    | Symbol       | Values |      |      | Unit | Note / Test Condition  |
|------------------------------|--------------|--------|------|------|------|--|
|                              |              | Min.   | Typ. | Max. |      |  |
| Input capacitance            | $C_{iss}$    | -      | 5360 | 6970 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$                                      |
| Output capacitance           | $C_{oss}$    | -      | 829  | 1078 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$                                      |
| Reverse transfer capacitance | $C_{rss}$    | -      | 37   | 65   | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$                                      |
| Turn-on delay time           | $t_{d(on)}$  | -      | 16.2 | -    | ns   | $V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=83\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Rise time                    | $t_r$        | -      | 9.7  | -    | ns   | $V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=83\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Turn-off delay time          | $t_{d(off)}$ | -      | 35   | -    | ns   | $V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=83\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Fall time                    | $t_f$        | -      | 9.8  | -    | ns   | $V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=83\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |

**Table 6 Gate charge characteristics<sup>2)</sup>**

| Parameter                          | Symbol        | Values |      |      | Unit | Note / Test Condition   |
|------------------------------------|---------------|--------|------|------|------|---|
|                                    |               | Min.   | Typ. | Max. |      |   |
| Gate to source charge              | $Q_{gs}$      | -      | 25   | -    | nC   | $V_{DD}=50\text{ V}$ , $I_D=83\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge <sup>1)</sup> | $Q_{gd}$      | -      | 16   | 23   | nC   | $V_{DD}=50\text{ V}$ , $I_D=83\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge                   | $Q_{sw}$      | -      | 25   | -    | nC   | $V_{DD}=50\text{ V}$ , $I_D=83\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total <sup>1)</sup>    | $Q_g$         | -      | 76   | 95   | nC   | $V_{DD}=50\text{ V}$ , $I_D=83\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage               | $V_{plateau}$ | -      | 4.7  | -    | V    | $V_{DD}=50\text{ V}$ , $I_D=83\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Output charge <sup>1)</sup>        | $Q_{oss}$     | -      | 98   | 130  | nC   | $V_{DD}=50\text{ V}$ , $V_{GS}=0\text{ V}$                                  |

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

| Parameter                             | Symbol        | Values |      |      | Unit | Note / Test Condition                                       |
|---------------------------------------|---------------|--------|------|------|------|---|
|                                       |               | Min.   | Typ. | Max. |      |   |
| Diode continuous forward current      | $I_S$         | -      | -    | 156  | A    | $T_C=25\text{ °C}$  |
| Diode pulse current                   | $I_{S,pulse}$ | -      | -    | 624  | A    | $T_C=25\text{ °C}$  |
| Diode forward voltage                 | $V_{SD}$      | -      | 0.9  | 1.2  | V    | $V_{GS}=0\text{ V}, I_F=83\text{ A}, T_j=25\text{ °C}$      |
| Reverse recovery time <sup>1)</sup>   | $t_{rr}$      | -      | 62   | 124  | ns   | $V_R=50\text{ V}, I_F=83, di_F/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge <sup>1)</sup> | $Q_{rr}$      | -      | 103  | 206  | nC   | $V_R=50\text{ V}, I_F=83, di_F/dt=100\text{ A}/\mu\text{s}$ |

<sup>1)</sup> Defined by design. Not subject to production test.

### 4 Electrical characteristics diagrams

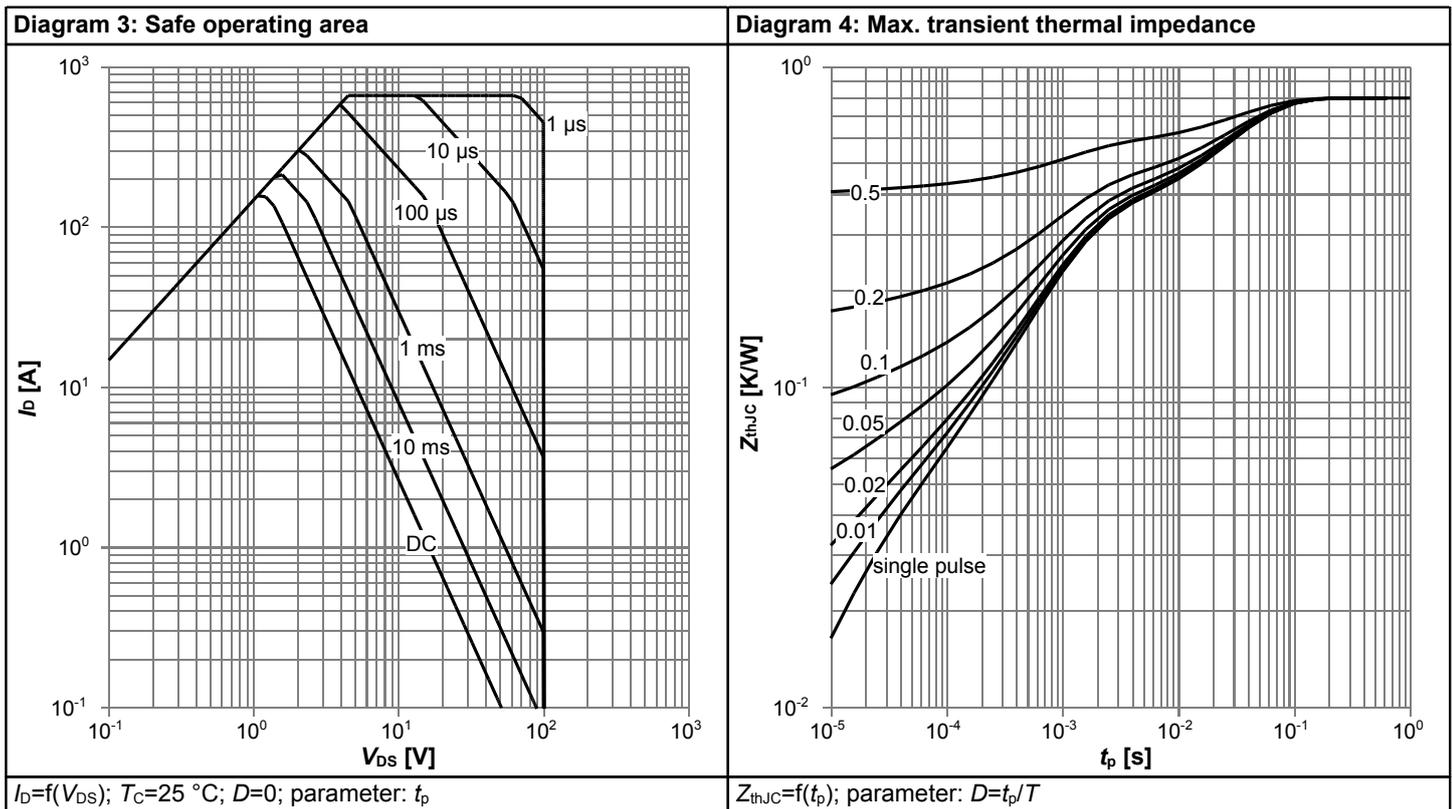
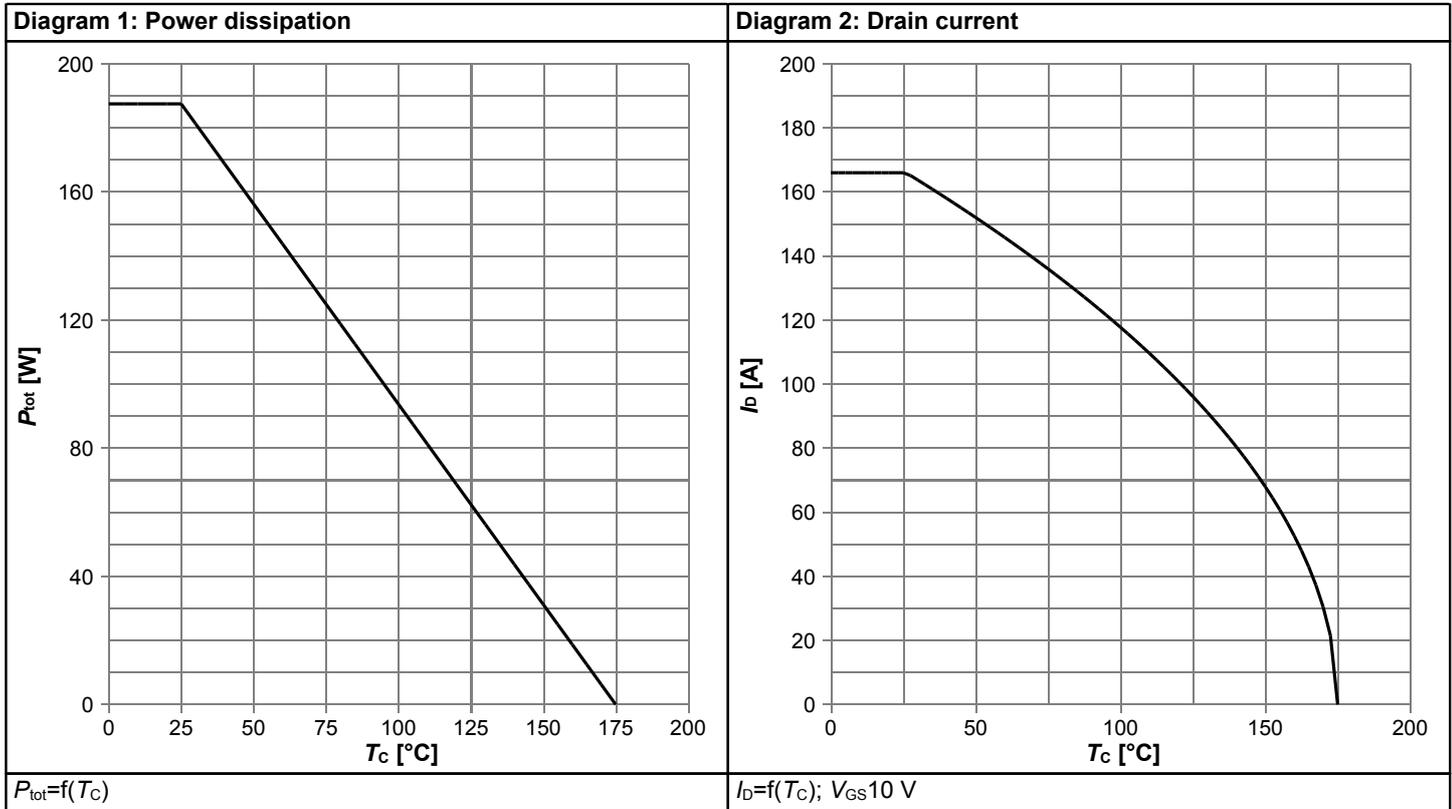
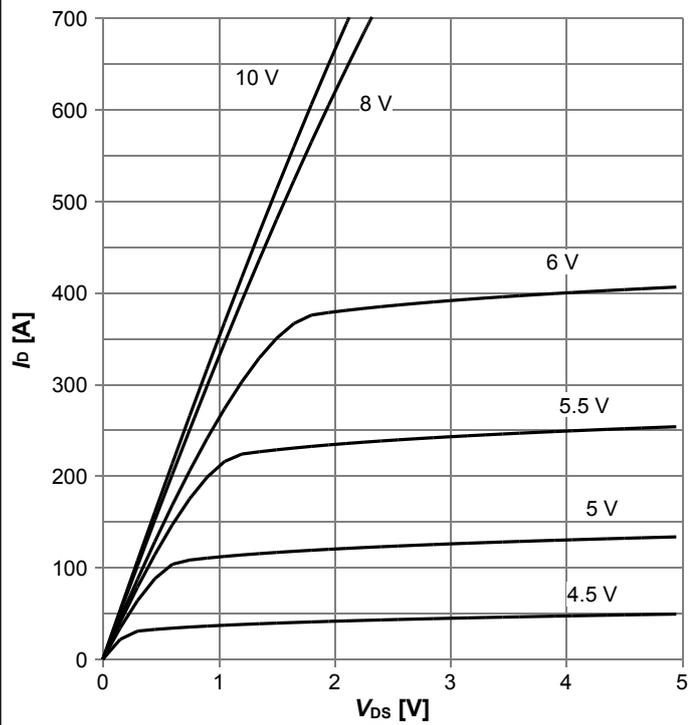
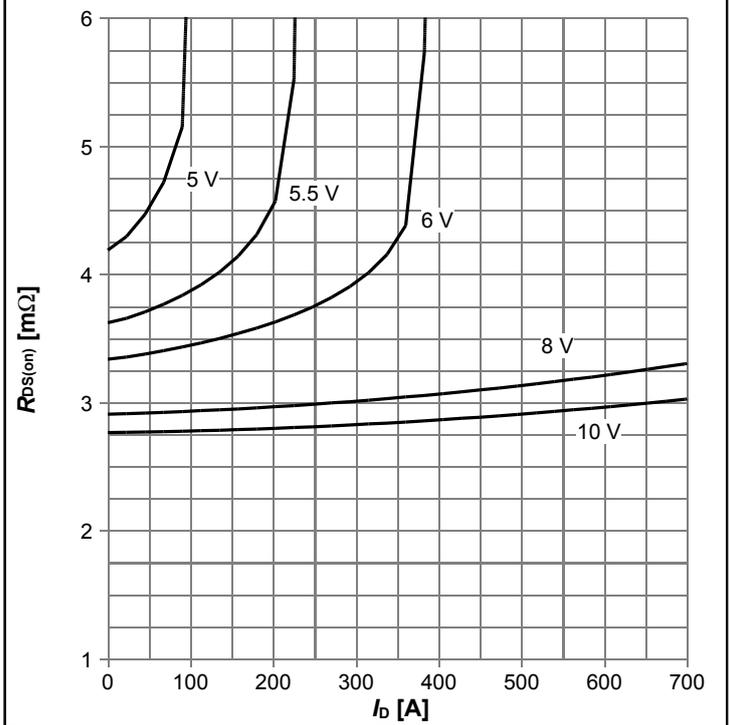


Diagram 5: Typ. output characteristics



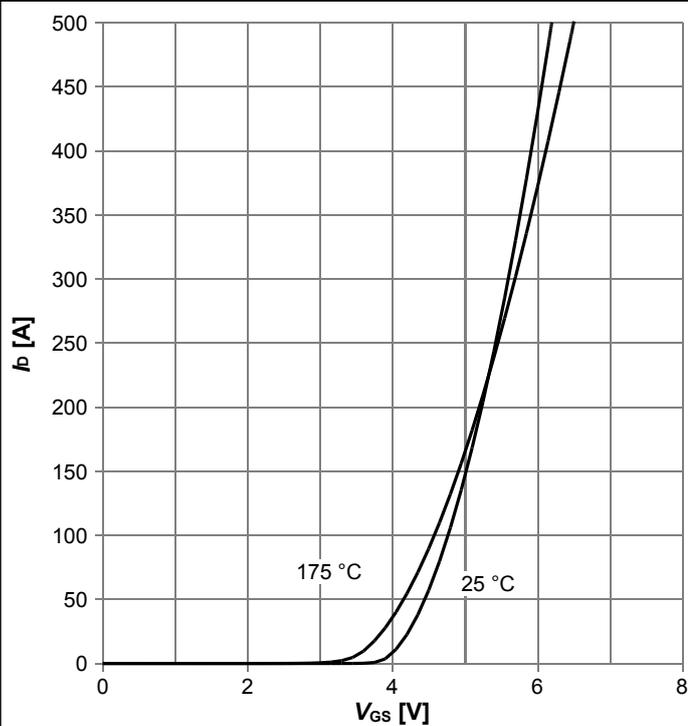
$I_D = f(V_{DS}); T_j = 25^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



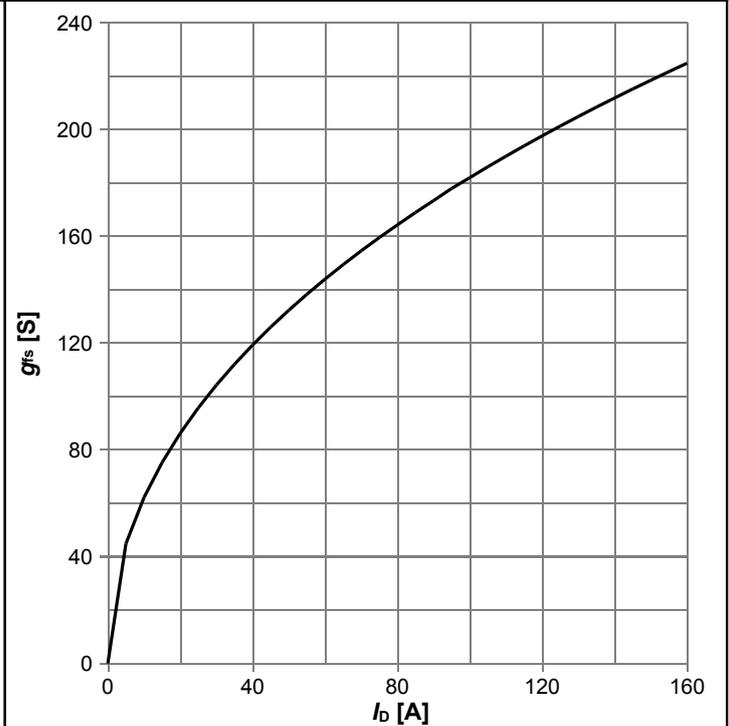
$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



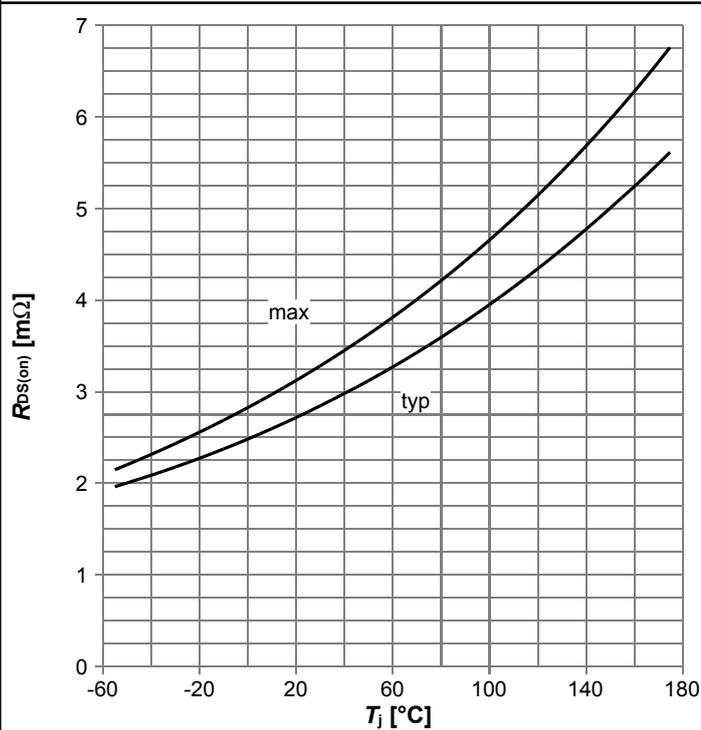
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max};$  parameter:  $T_j$

Diagram 8: Typ. forward transconductance



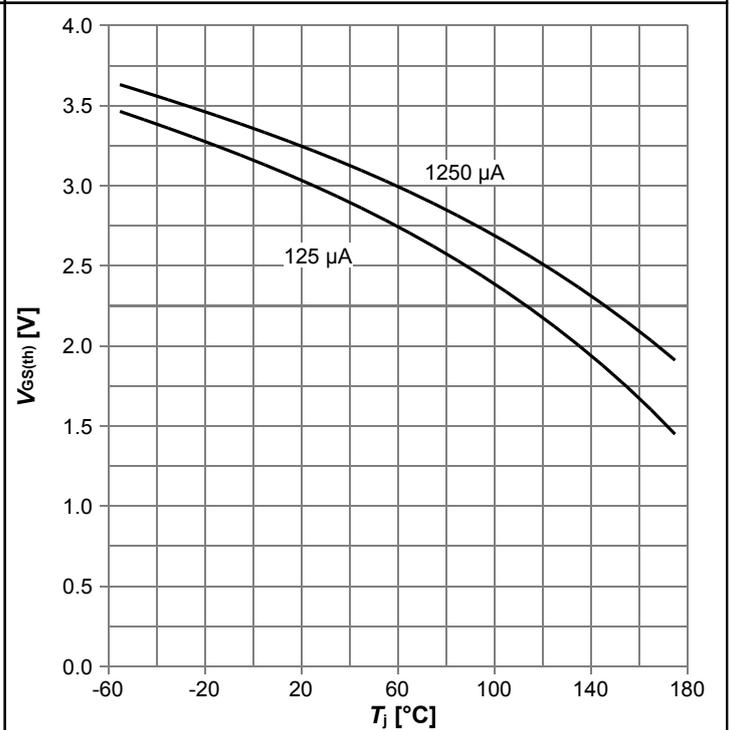
$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



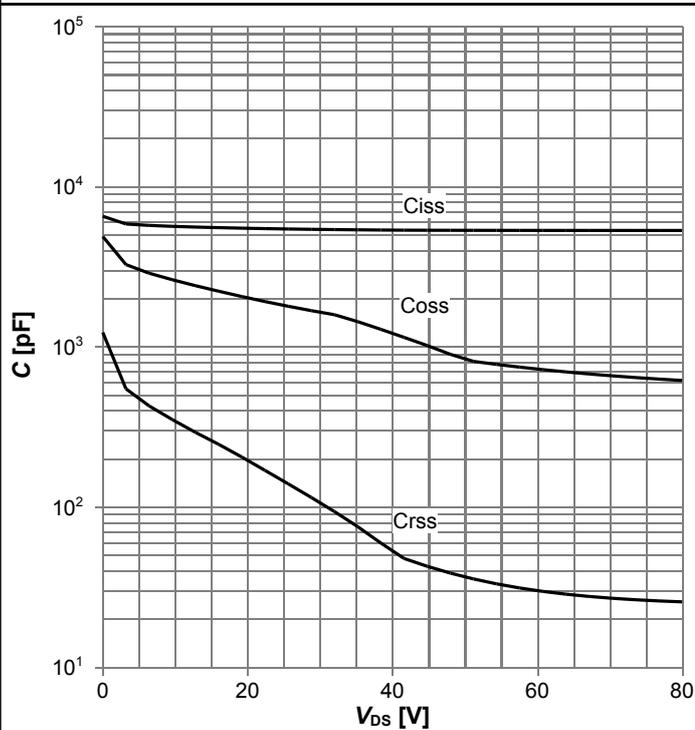
$R_{DS(on)}=f(T_j)$ ;  $I_D=83\text{ A}$ ;  $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



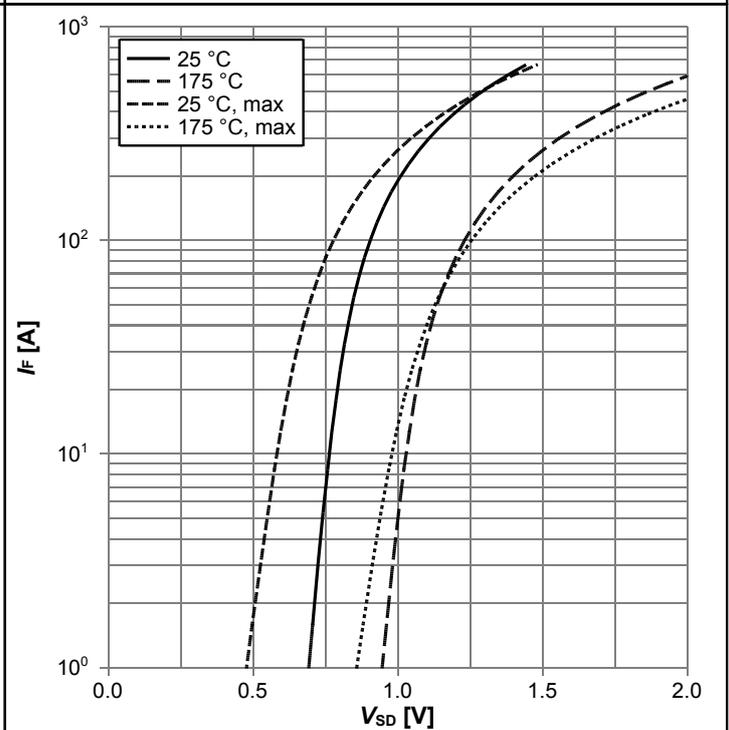
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



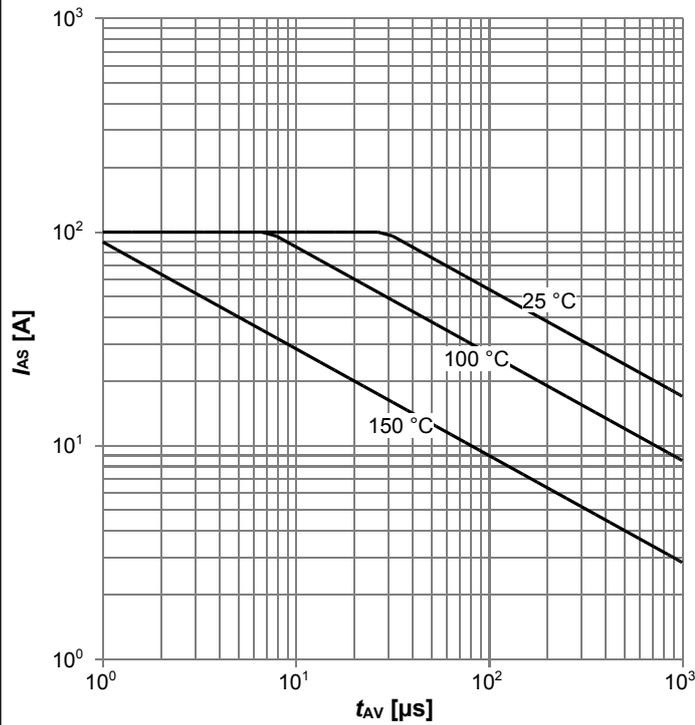
$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



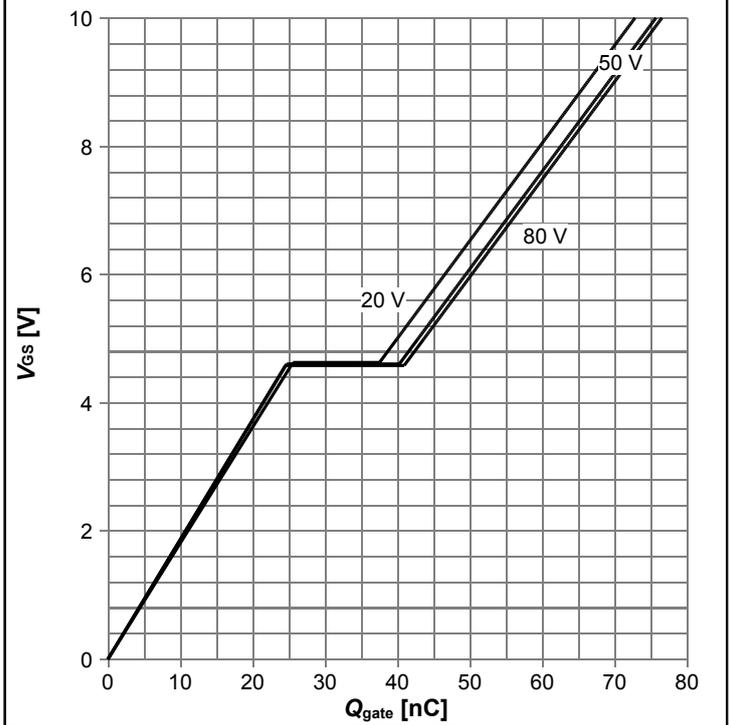
$I_F=f(V_{SD})$ ; parameter:  $T_j$

**Diagram 13: Avalanche characteristics**



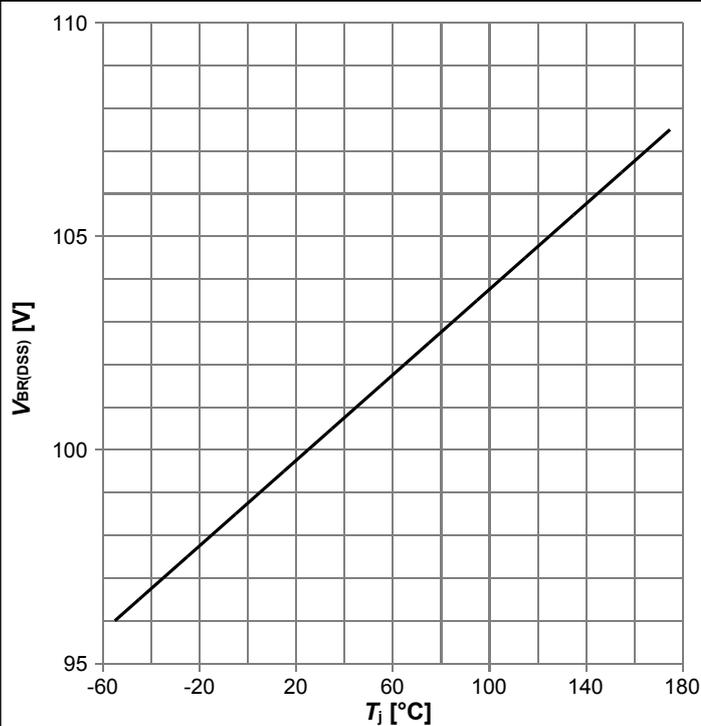
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

**Diagram 14: Typ. gate charge**



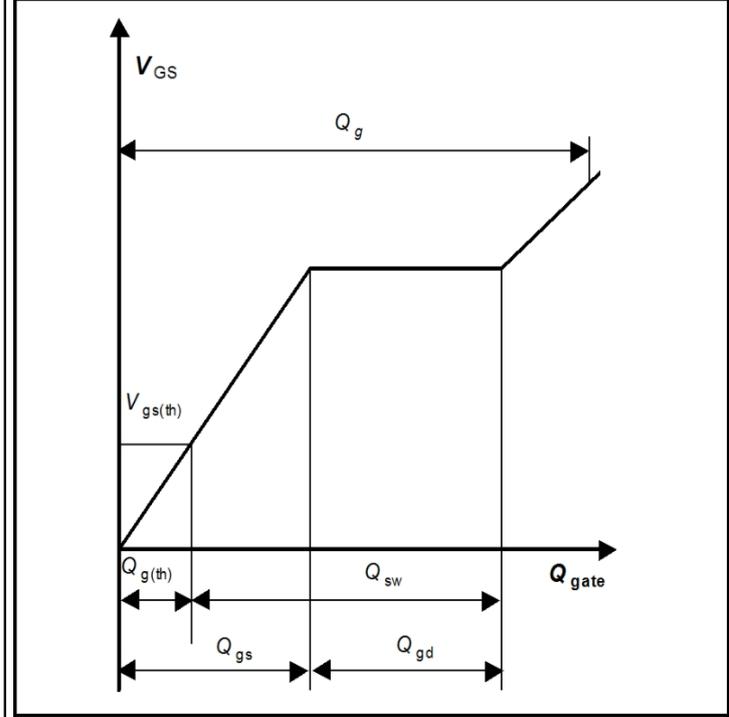
$V_{GS}=f(Q_{gate})$ ,  $I_D=83$  A pulsed; parameter:  $V_{DD}$

**Diagram 15: Drain-source breakdown voltage**

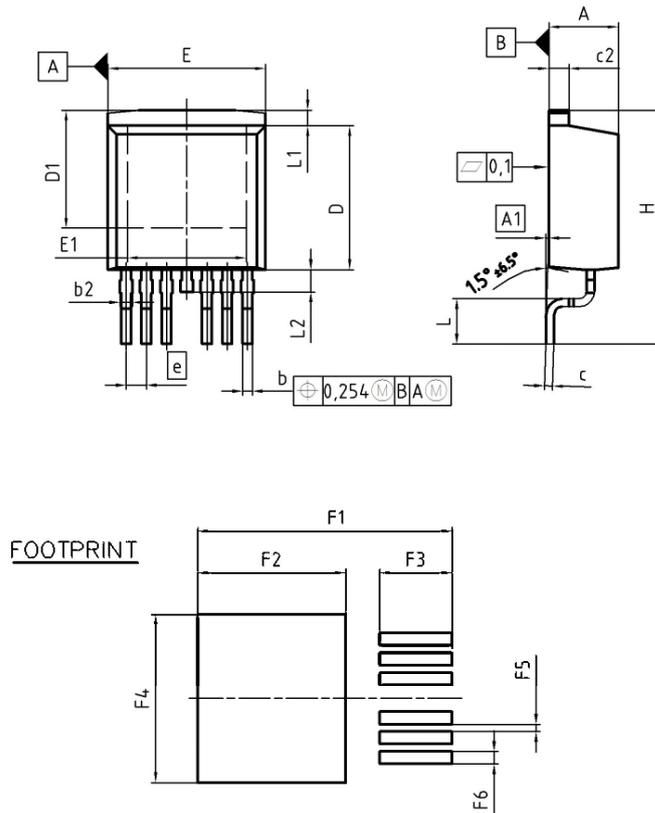


$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1$  mA

**Gate charge waveforms**



## 5 Package Outlines



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 0.00        | 0.25  | 0.000  | 0.010 |
| b   | 0.50        | 0.70  | 0.020  | 0.028 |
| b2  | 0.50        | 1.00  | 0.020  | 0.039 |
| c   | 0.33        | 0.65  | 0.013  | 0.026 |
| c2  | 1.17        | 1.40  | 0.046  | 0.055 |
| D   | 8.51        | 9.45  | 0.335  | 0.372 |
| D1  | 6.90        | 7.90  | 0.272  | 0.311 |
| E   | 9.80        | 10.31 | 0.386  | 0.406 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 1.27        |       | 0.050  |       |
| N   | 6           |       | 6      |       |
| H   | 14.61       | 15.88 | 0.575  | 0.625 |
| L   | 2.29        | 3.00  | 0.090  | 0.118 |
| L1  | 0.70        | 1.60  | 0.028  | 0.063 |
| L2  | 1.00        | 1.78  | 0.039  | 0.070 |
| F1  | 16.05       | 16.25 | 0.632  | 0.640 |
| F2  | 9.30        | 9.50  | 0.366  | 0.374 |
| F3  | 4.50        | 4.70  | 0.177  | 0.185 |
| F4  | 10.70       | 10.90 | 0.421  | 0.429 |
| F5  | 0.37        | 0.57  | 0.015  | 0.022 |
| F6  | 0.70        | 0.90  | 0.028  | 0.035 |

DOCUMENT NO.  
Z8B00134765

SCALE

EUROPEAN PROJECTION

ISSUE DATE  
05-11-2007

REVISION  
01

Figure 1 Outline PG-TO263-7, dimensions in mm/inches

## Revision History

IPB032N10N5

**Revision: 2016-12-12, Rev. 2.0**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0      | 2016-12-12 | Release of final version                     |

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**Infineon Technologies AG**  
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